

# JIEJIE MICROELECTRONICS CO., LTD.

## JSTE30P45A

# 30A Schottky Barrier Rectifier

Rev.1.1

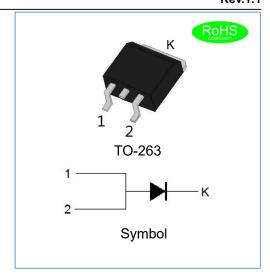
#### **DESCRIPTION**

- ♦ Trench MOS barrier schottky technology
- ♦ Low stored charge majority carrier conduction
- ♦ Ultra low forward voltage drop
- ♦ Low leakage current
- ♦ Low power loss and high efficiency
- ♦ High forward surge capacity

#### **MECHANICAL DATA**

♦ Case: TO-263 molded plastic

→ Terminals: Solder plated, solderable per J-STD-002



### ABSOLUTE MAXIMUM RATING (Rating at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbol	JSTE30P45A	Unit
Maximum repetitive peak reverse voltage	$V_{RRM}$	45	\ \
Maximum RMS voltage	V <sub>RMS</sub>	31.5	٧
Maximum DC blocking voltage	V <sub>DC</sub>	45	V
Average forward current	I <sub>F(AV)</sub>	30	Α
Peak forward surge current: 8.3ms single half sine-wave superimposed on rated load	I <sub>FSM</sub>	290	Α
Operating junction temperature range	Tj	-55 to +150	Š
Storage temperature range	T <sub>stg</sub>	-55 to +150	$\mathbb{C}$

## **ELECTRICAL CHARACTERISTICS**(Rating at 25°C ambient temperature unless otherwise specified.)

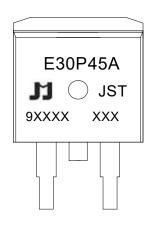
Paramete	Symbol	Min.	Тур.	Max.	Unit	
	I <sub>F</sub> =0.5A, T <sub>A</sub> =25℃		-	0.32	-	- V
Fanyard valtage	I <sub>F</sub> =15A, T <sub>A</sub> =25℃	V	-	0.45	-	
Forward voltage	I <sub>F</sub> =20A, T <sub>A</sub> =25℃	V <sub>F</sub>	-	0.47	-	
	I <sub>F</sub> =30A, T <sub>A</sub> =25℃		-	0.49	0.56	
Deveree current	V <sub>R</sub> =45V, T <sub>A</sub> =25°C	_	-	-	100	μA
Reverse current	V <sub>R</sub> =45V, T <sub>A</sub> =125°C	l <sub>R</sub>	-	-	50	mA
Reverse recovery time	I <sub>F</sub> =3A, dI/dt=100A/μs	t <sub>rr</sub>	-	-	30	ns
Junction capacitance	V <sub>R</sub> =5V <sub>DC</sub> , f=1MHz	CJ	-	750	-	pF



# THERMAL RESISTANCES

Symbol	Parameter	JSTE30P45A	Unit
R <sub>th(j-c)</sub>	Thermal resistances from junction to case	2.1	°C/W

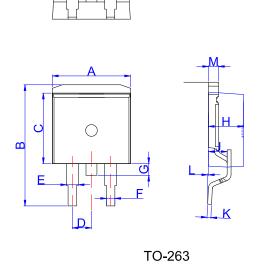
## **MARKING**



10	0 1 111 D : D 115			
JS	Schottky Barrier Rectifier			
Т	Trench technology			
Е	Package: TO-263			
30	I <sub>F(AV)</sub> =30A			
Р	Photovoltaic			
45	V <sub>RRM</sub> :45V			
Α	Version			

9	Year code(8:2018,9:2019,)			
XX	Week code			
XX	Chip code			
XXX	Package lot number			

# PACKAGE MECHANICAL DATA



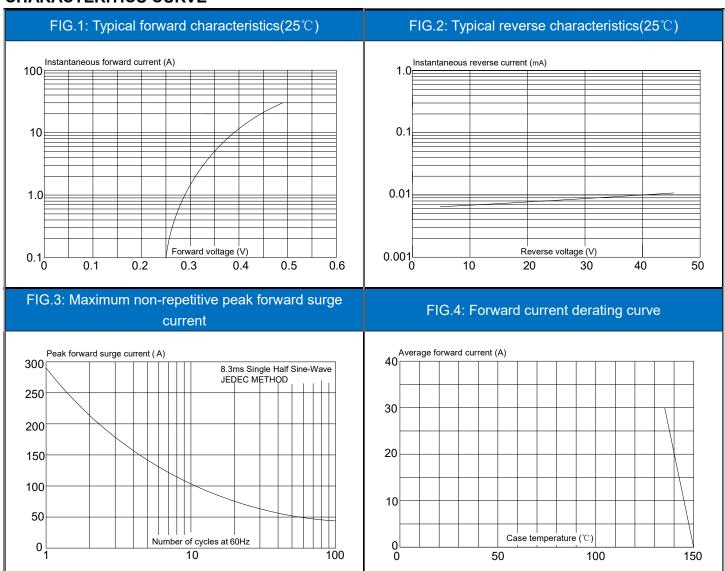
	Dimensions					
Ref.	Millimeters					
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	9.90		10.20	0.390		0.402
В	14.70		15.80	0.579		0.622
С	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
Н	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
М	1.25		1.35	0.049		0.053



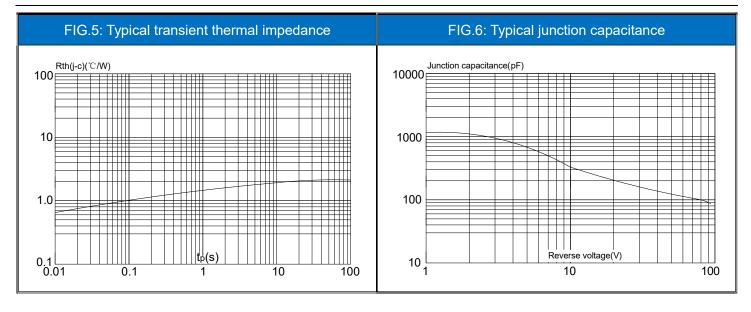
#### **PACKAGE INFORMATION-TO-263**

OUTLINE	OUTLINE UNIT WEIGHT (g/PCS) TYP		PER CARTON (PCS)	
TUBE	1.514	50	5,000	

#### **CHARACTERITICS CURVE**







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